

# UP0KG8D

Silicon epitaxial planar type (SBD)  
Silicon PNP epitaxial planar type (Tr)

For digital circuits

## ■ Features

- Two elements incorporated into one package (SBD + Tr)
- Costs can be reduced through downsizing of the equipment and reduction of the number of parts

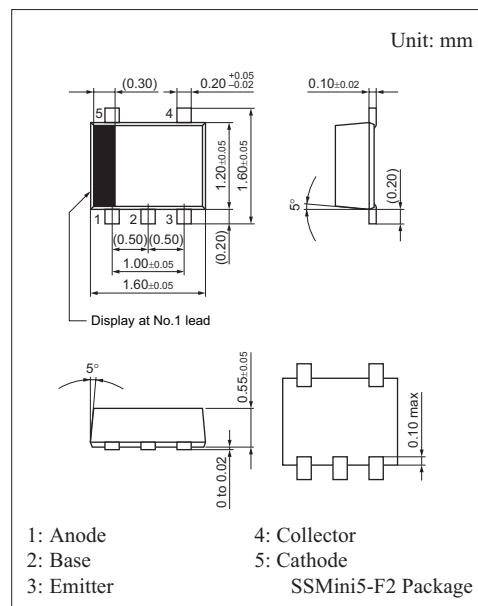
## ■ Basic Part Number

- MA2SD24 + UNR31A3

## ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

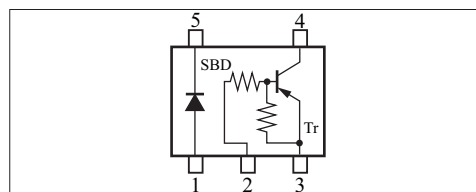
	Parameter	Symbol	Rating	Unit
SBD	Reverse voltage	$V_R$	20	V
	Repetitive peak reverse voltage	$V_{RRM}$	20	V
	Forward current (Average)	$I_{F(AV)}$	200	mA
	Peak forward current	$I_{FM}$	300	mA
	Non-repetitive peak forward surge current	$I_{FSM}$	1	A
Tr	Collector-base voltage (Emitter open)	$V_{CBO}$	-50	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	-50	V
	Collector current	$I_C$	-80	mA
Overall	Total power dissipation	$P_T$	125	mW
	Junction temperature	$T_j$	125	$^\circ\text{C}$
	Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

Note) \*: 50 Hz sine wave 1 cycle (Non-repetitive peak current)



Marking Symbol: 6K

Internal Connection



■ Electrical Characteristics  $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

• SBD

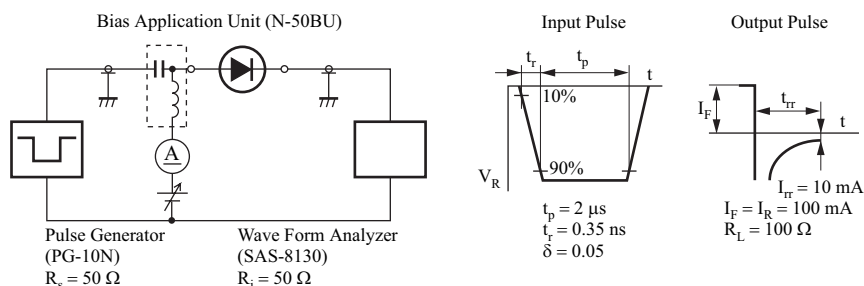
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	$V_F$	$I_F = 200 \text{ mA}$		0.50	0.58	V
Reverse current	$I_R$	$V_R = 10 \text{ V}$		0.1	1	$\mu\text{A}$
Terminal capacitance	$C_t$	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$		25		pF
Reverse recovery time *	$t_{rr}$	$I_F = I_R = 100 \text{ mA}, I_{rr} = 10 \text{ mA}, R_L = 100 \Omega$		3		ns

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.

2. Absolute frequency of input and output is 250 MHz

2. This product is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.

3. \*:  $t_{rr}$  measurement circuit

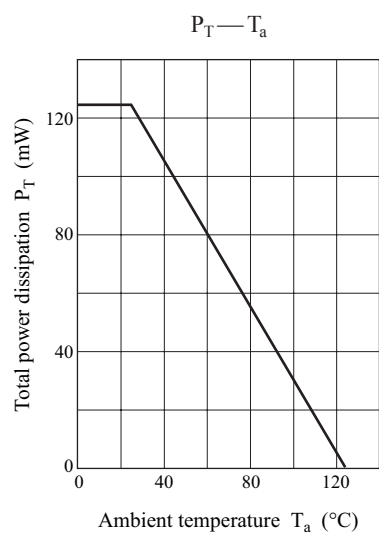


• Tr2

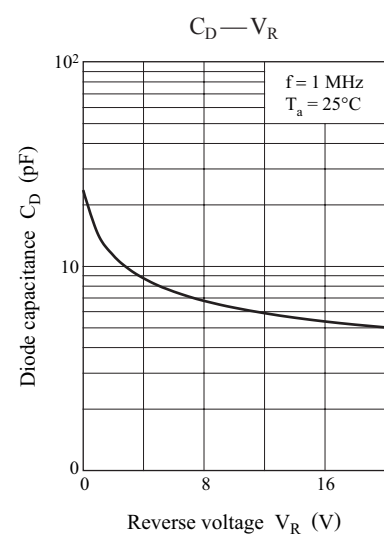
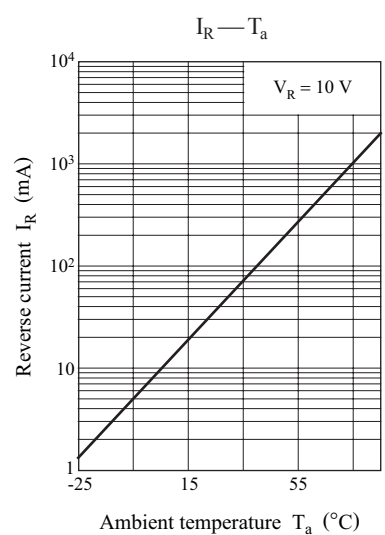
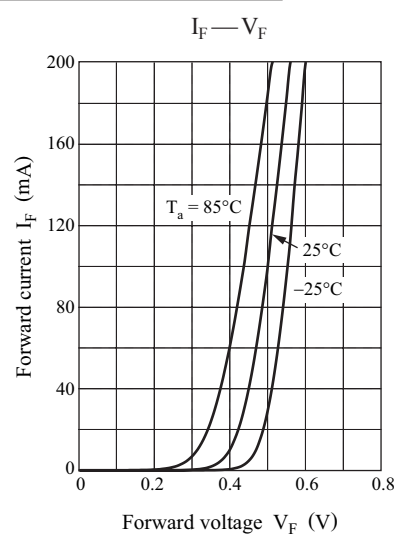
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = -10 \mu\text{A}, I_E = 0$	-50			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = -2 \text{ mA}, I_B = 0$	-50			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -50 \text{ V}, I_E = 0$			-0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = -50 \text{ V}, I_B = 0$			-0.5	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = -6 \text{ V}, I_C = 0$			-0.1	mA
Forward current transfer ratio	$h_{FE}$	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	80			—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10 \text{ mA}, I_B = -0.3 \text{ mA}$			-0.25	V
Output voltage high-level	$V_{OH}$	$V_{CC} = -5 \text{ V}, V_B = -0.5 \text{ V}, R_L = 1 \text{ k}\Omega$	-4.9			V
Output voltage low-level	$V_{OL}$	$V_{CC} = -5 \text{ V}, V_B = -3.5 \text{ V}, R_L = 1 \text{ k}\Omega$			-0.2	V
Input resistance	$R_1$		-30%	47	+30%	$\text{k}\Omega$
Resistance ratio	$R_1 / R_2$		0.8	1.0	1.2	—
Transition frequency	$f_T$	$V_{CB} = -10 \text{ V}, I_E = 2 \text{ mA}, f = 200 \text{ MHz}$		80		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

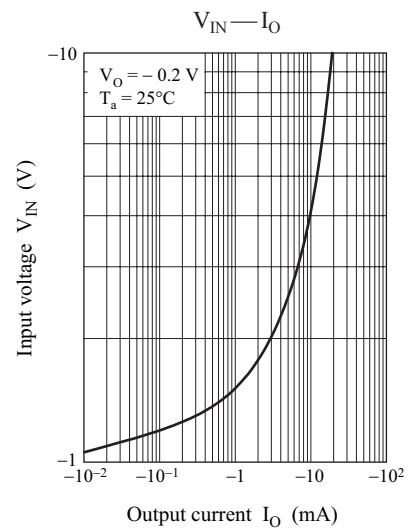
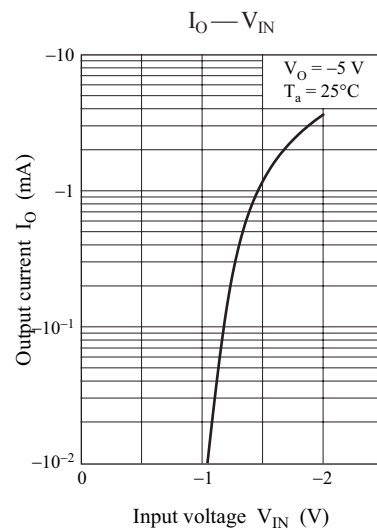
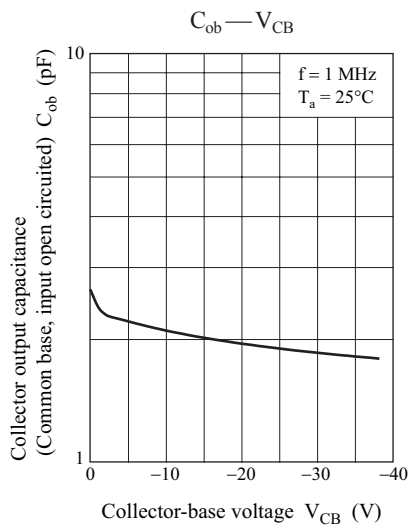
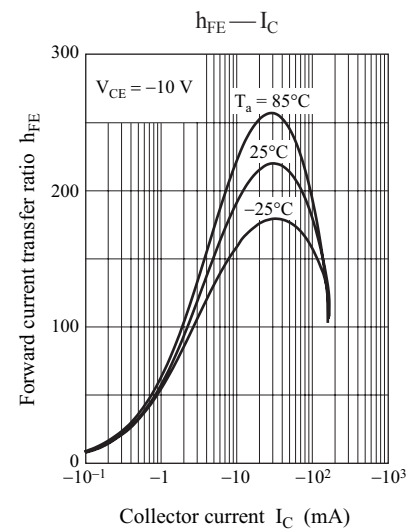
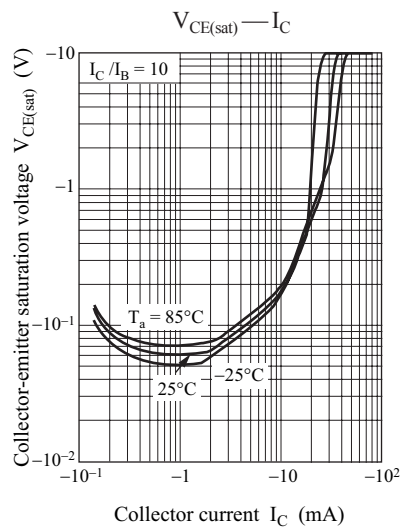
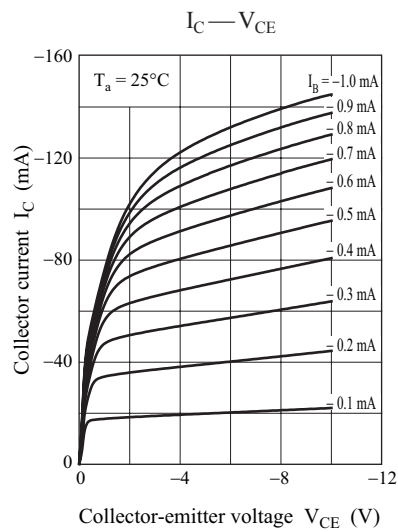
Common characteristics chart



Characteristics charts of SBD



Characteristics charts of Tr



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